



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BVDSS	Rds(on)	I _D T _A = +25°C
	750mΩ @ V _{GS} = -4.5V	-0.6A
-20V	1050mΩ @ V _{GS} = -2.5V	-0.5A
	1500mΩ @ V _{GS} = -1.8V	-0.45A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP.

- DC-DC converters
- Load switches
- · Power-management functions

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMP2900UWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

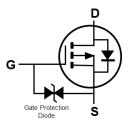
- Package: SOT323
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish—Matte Tin Annealed over Alloy 42 Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.006 grams (Approximate)



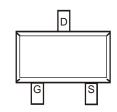


SOT323









Top View

Ordering Information (Note 4)

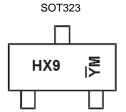
Part Number	Package	Packing		
Fait Number	Fackage	Qty.	Carrier	
DMP2900UWQ-7	SOT323	3,000	Tape & Reel	
DMP2900UWQ-13	SOT323	10,000	Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/



Marking Information



HX9 = Product Type Marking Code YM = Date Code Marking \overline{Y} = Year (ex: K = 2023) M = Month (ex: 9 = September)

Date Code Key

	1											
Year	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	J	K	L	М	N	0	Р	R	S	Т	U	V
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V _{DSS}	-20	V		
Gate-Source Voltage	Vgss	±6	V		
Continuous Drain Current (Note 5) V _{GS} = 4.5V	lD	-0.6 -0.5	А		
Maximum Body Diode Forward Current (Note 5)	Is	-0.45	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle=1%)			I _{DM}	-2.5	Α

Thermal Characteristics

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 6)		P _D	0.3	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	393	°C/W
Total Power Dissipation (Note 5)		PD	0.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	272	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Notes:

5. Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.6. Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout.



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

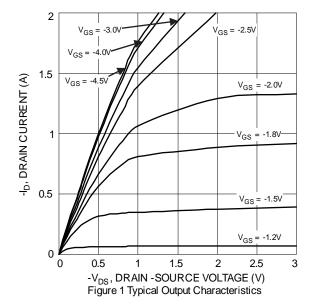
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 7)								
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	Vgs = 0V, ID = -250µA		
Zero Gate Voltage Drain Current T _J = +25°C	IDSS	_	_	-100	nA	V _{DS} = -20V, V _{GS} = 0V		
Gate-Source Leakage	Igss	_	_	±2.0	μΑ	$V_{GS} = \pm 4.5V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 7)	ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	Vgs(TH)	-0.5	1	-1.0	>	$V_{DS} = V_{GS}$, $I_D = -250\mu A$		
			_	0.75		$V_{GS} = -4.5V$, $I_D = -430mA$		
Static Drain-Source On-Resistance	R _{DS(ON)}	_	_	1.05	Ω	$V_{GS} = -2.5V, I_D = -300mA$		
		_	_	1.5		$V_{GS} = -1.8V, I_{D} = -150mA$		
Diode Forward Voltage	VsD	_	_	-1.2	٧	$V_{GS} = 0V, I_{S} = -150mA$		
DYNAMIC CHARACTERISTICS (Note 8)								
Input Capacitance	Ciss		49		pF			
Output Capacitance	Coss	_	12	_	pF	V _{DS} = -16V, V _{GS} = 0V f = 1.0MHz		
Reverse Transfer Capacitance	Crss	_	3.4	_	pF	1 = 1.0ivii 12		
Total Gate Charge	Qg		0.7		рС	V 45V V 40V		
Gate-Source Charge	Qgs		0.1		рС	V _G S = -4.5V, V _D S = -10V		
Gate-Drain Charge	Qgd		0.1		рС	ID = -230IIIA		
Turn-On Delay Time	t _{D(on)}	_	16	_	ns			
Turn-On Rise Time	t _R	_	15	_	ns	$V_{DD} = -10V, V_{GS} = -4.5V$ $R_{L} = 47\Omega. R_{G} = 10\Omega$		
Turn-Off Delay Time	t _{D(off)}	_	213	_	ns	$RL = 47\Omega$, $RG = 10\Omega$ ID = -200 mA		
Turn-Off Fall Time	tF	_	89	_	ns	10 - 2001111		
Reverse Recovery Time	t _{RR}	_	10.5	_	ns	I 1 00 dl/dt = 1000/u-		
Reverse Recovery Charge	Qrr	_	1.8	_	nC	IF = 1.0A, dI/dt = 100A/μs		

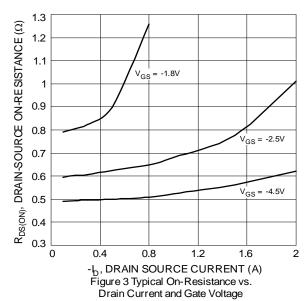
Notes:

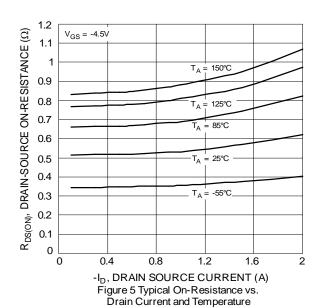
^{7.} Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to production testing.

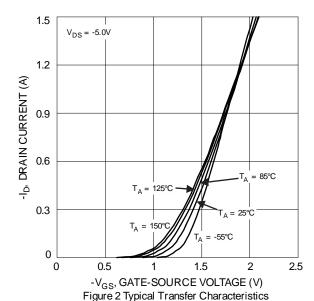


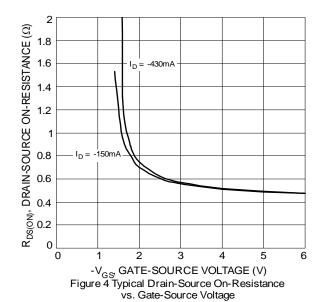


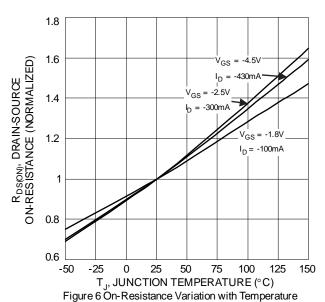








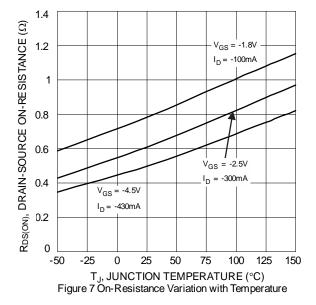


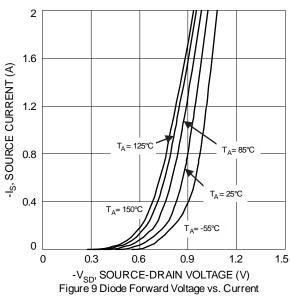


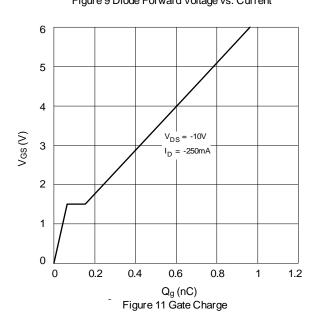
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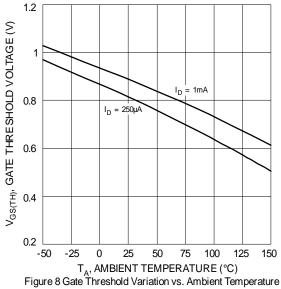


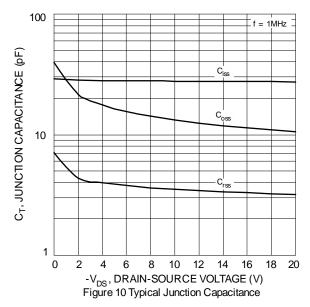


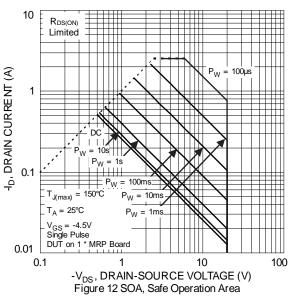














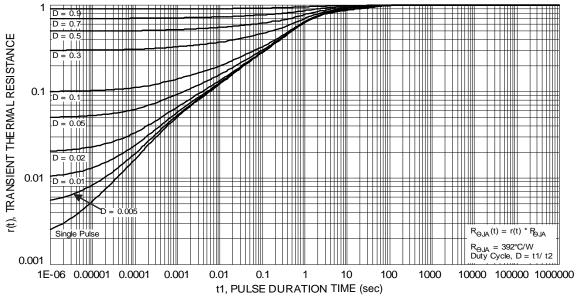


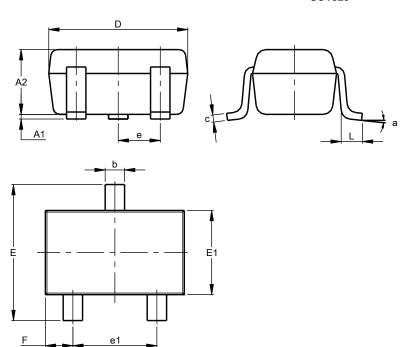
Figure 13 Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT323



SOT323							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.90	1.00	0.95				
b	0.25	0.40	0.30				
C	0.10	0.18	0.11				
D	1.80	2.20	2.15				
Е	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е	C).650 B	SC				
e1	1.20	1.40	1.30				
F	0.375	0.475	0.425				
L	0.25	0.40	0.30				
а	0°	8°					
All	Dimen	sions i	in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.470
Υ	0.600

2.500

Y1

SOT323



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